

Abstract

Method for fabricating thin metal-containing layers having low electrical resistance

The invention relates to a method for fabricating thin metal-containing layers (5C) having low electrical resistance, firstly a metal-containing starting layer (5A) having a first grain size being formed on a carrier material (2). Afterwards, a locally delimited thermal region (W) is produced and moved in the metal-containing starting layer (5A) in such a way that a recrystallization of the metal-containing starting layer (5A) is carried out for the purpose of producing the metal-containing layer (5C) having a second grain size, which is enlarged with respect to the first grain size. A metal-containing layer having improved electrical properties is obtained in this way.

Figure 3